

PATENT
MB&P Ref. No.: I 3527-RO/SEI
Atty. Dkt. No. INFN/MB0061

IN THE SPECIFICATION:

Please replace paragraph [0058] with the following amended paragraph:

[0058] Therefore, during the immediately subsequent metallization step, contact is not made with the emitter contact 14, which in this embodiment of the semiconductor device is referred to as the second (higher) contact. On account of the fact that contact is not made with the emitter contact 14 (the second contact) at this process stage, the patterning of the contact holes 32 [[33]], i.e., the CMP BPSG polishing step and the CT etch plasma etching step, does not need to be adapted to make simultaneous contact with the first and second contacts, which is complex in terms of the process engineering.